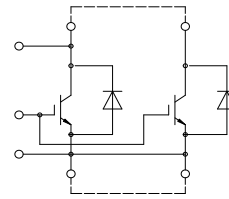


IHM-B 模块 采用第三代高速沟槽栅/场终止IGBT和第三代发射极控制二极管  
 IHM-B module with fast Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode



external connection  
(to be done)

$V_{CES} = 3300V$   
 $I_{C\ nom} = 1000A / I_{CRM} = 2000A$

### 潜在应用

- UPS系统
- 中压变流器
- 斩波应用
- 牵引变流器
- 电机传动
- 风力发电机

### Potential Applications

- UPS systems
- Medium voltage converters
- Chopper applications
- Traction drives
- Motor drives
- Wind turbines

### 电气特性

- $T_{vj\ op} = 150^{\circ}C$
- $V_{CEsat}$  带正温度系数
- 低  $V_{CEsat}$
- 低开关损耗
- 无与伦比的坚固性
- 高直流电压稳定性
- 高短路能力

### Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- $V_{CEsat}$  with positive temperature coefficient
- Low  $V_{CEsat}$
- Low switching losses
- Unbeatable robustness
- High DC stability
- High short-circuit capability

### 机械特性

- IHM B 封装
- 封装的 CTI > 600
- 碳化硅铝 (AlSiC) 基板提供更高的温度循环能力
- 绝缘的基板

### Mechanical Features

- IHM B housing
- Package with CTI > 600
- AlSiC base plate for increased thermal cycling capability
- Isolated base plate

## Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

## IGBT, 逆变器 / IGBT, Inverter

### 最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CES}$	3300 3300	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}$ , $T_{vj\text{max}} = 150^{\circ}\text{C}$	$I_{CDC}$	1000	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	2000	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

### 特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1000\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,55 3,00 3,15	3,10 3,45	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 48,0\text{ mA}$ , $V_{CE} = V_{GE}$ , $T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,20	5,80	6,40 V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}$ , $V_{CE} = 1800\text{ V}$		$Q_G$	28,0		$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	0,63		$\Omega$
输入电容 Input capacitance	$f = 1000\text{ kHz}$ , $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$		$C_{ies}$	190		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}$ , $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$		$C_{res}$	4,00		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 3300\text{ V}$ , $V_{GE} = 0\text{ V}$ , $T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = 20\text{ V}$ , $T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 0,71\ \Omega$ , $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{don}$	0,35 0,38 0,38		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 0,71\ \Omega$ , $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,35 0,38 0,38		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,3\ \Omega$ , $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{doff}$	3,00 3,20 3,20		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,3\ \Omega$ , $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,30 0,35 0,35		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ , $L_{\sigma} = 85\text{ nH}$ $di/dt = 3000\text{ A}/\mu\text{s}$ ( $T_{vj} = 150^{\circ}\text{C}$ ) $V_{GE} = -15 / 15\text{ V}$ , $R_{Gon} = 0,71\ \Omega$ $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	1250 1700 1950		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1000\text{ A}$ , $V_{CE} = 1800\text{ V}$ , $L_{\sigma} = 85\text{ nH}$ $du/dt = 2100\text{ V}/\mu\text{s}$ ( $T_{vj} = 150^{\circ}\text{C}$ ) $V_{GE} = -15 / 15\text{ V}$ , $R_{Goff} = 2,3\ \Omega$ $C_{GE} = 220\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	1050 1400 1550		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}$ , $V_{CC} = 2500\text{ V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}$ , $T_{vj} = 150^{\circ}\text{C}$		$I_{sc}$	4200		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$		11,1	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	14,5		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

## 二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{RRM}$	3300 3300	V
连续正向直流电流 Continuous DC forward current		$I_F$	1000	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	2000	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	260 245	$\text{kA}^2\text{s}$ $\text{kA}^2\text{s}$
最大损耗功率 Maximum power dissipation	$T_{vj} = 150^{\circ}\text{C}$	$P_{RQM}$	1600	kW
最小开通时间 Minimum turn-on time		$t_{on\ min}$	10,0	$\mu\text{s}$

## 特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1000\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1000\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1000\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	3,10 2,75 2,65	3,85 3,25	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1000\text{ A}, -di_F/dt = 3000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	1000 1200 1250		A A A
恢复电荷 Recovered charge	$I_F = 1000\text{ A}, -di_F/dt = 3000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	450 900 1050		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1000\text{ A}, -di_F/dt = 3000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	450 1100 1300		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$		19,8	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$		16,5	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40	150	$^{\circ}\text{C}$

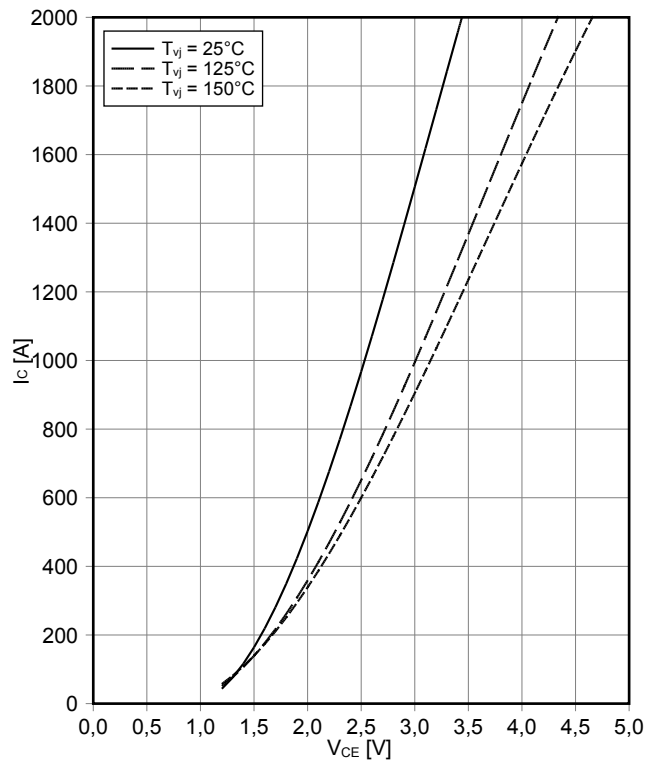
## 模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	6,0		kV
局部放电停止电压 Partial discharge extinction voltage	RMS, f = 50 Hz, Q <sub>PD</sub> ≤ 10 pC	V <sub>ISOL</sub>	2,6		kV
DC 稳定性 DC stability	T <sub>vj</sub> = 25°C, 100 fit	V <sub>CE D</sub>	2100		V
模块基板材料 Material of module baseplate			AlSiC		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		32,2		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,1		mm
相对电痕指数 Comperative tracking index		CTI	> 600		
min.    typ.    max.					
杂散电感, 模块 Stray inductance module		L <sub>sCE</sub>	9,0		nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T <sub>c</sub> = 25°C, 每个开关 / per switch	R <sub>CC+EE'</sub>	0,19		mΩ
储存温度 Storage temperature		T <sub>stg</sub>	-40	150	°C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25	5,75	Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,8 8,0	- 10	2,1 Nm Nm
重量 Weight		G	800		g

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

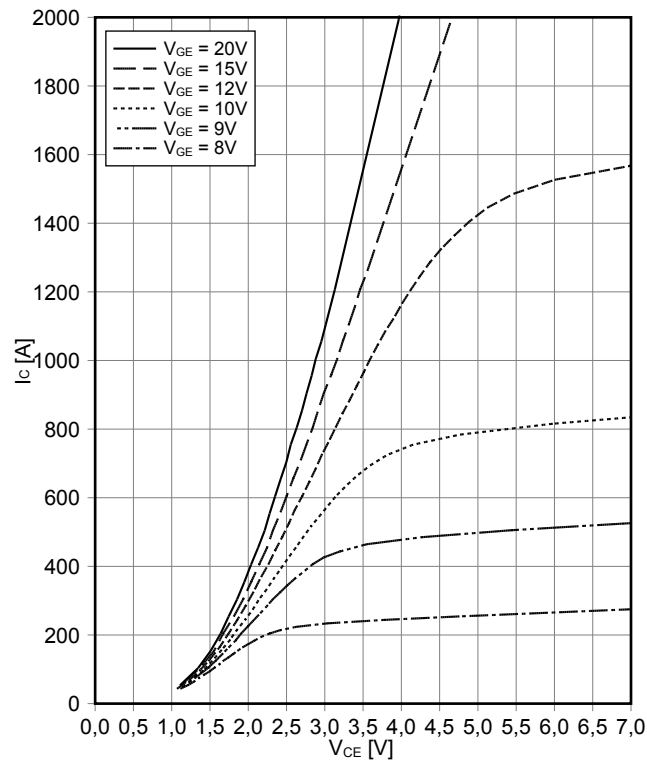
$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

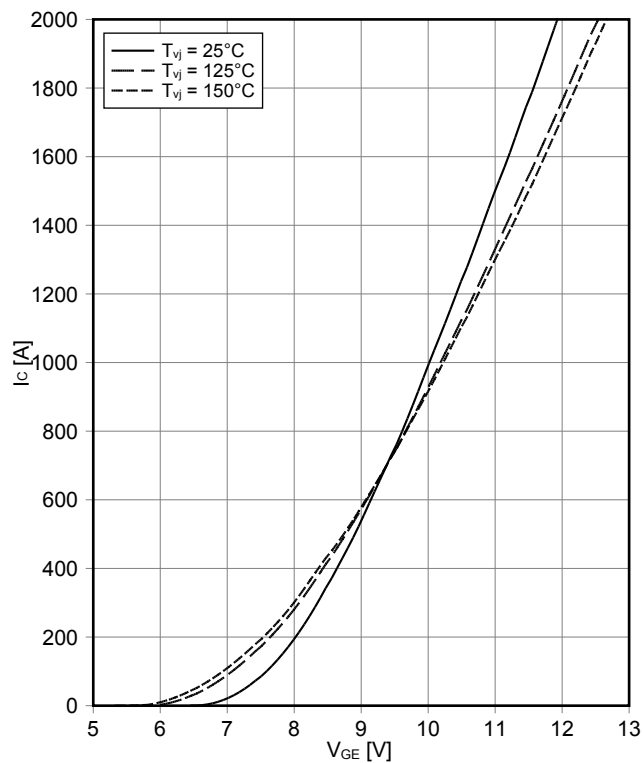
$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

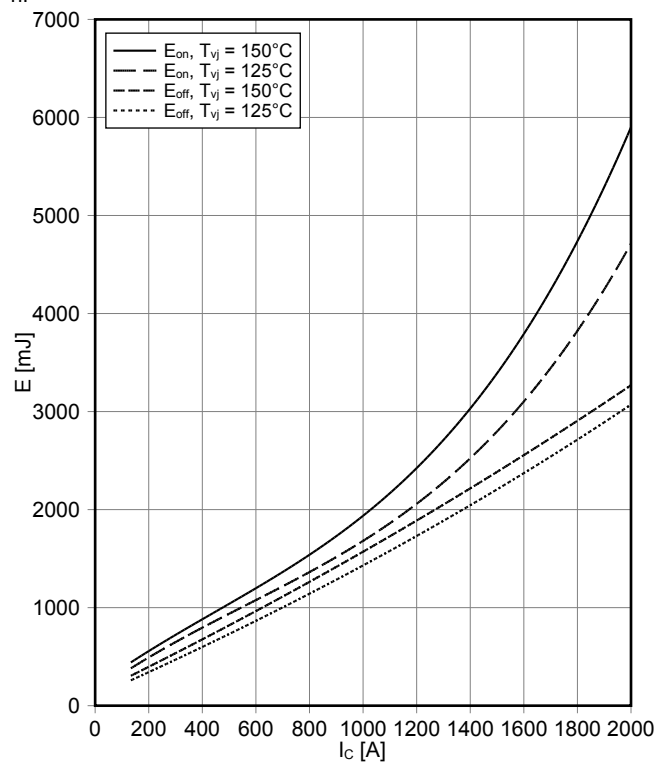
$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 0.71\ \Omega$ ,  $R_{Goff} = 2.3\ \Omega$ ,  $V_{CE} = 1800\text{ V}$ ,  $C_{GE} = 220\text{ nF}$

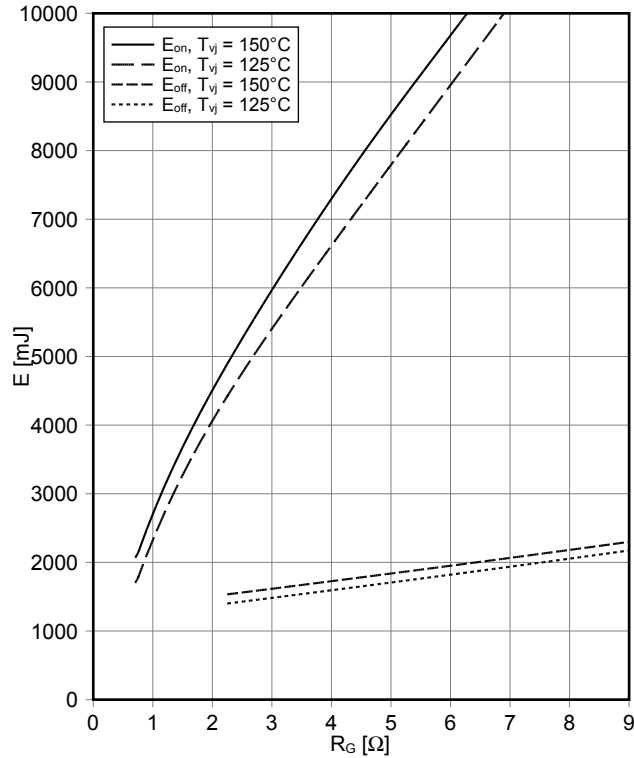


开关损耗 IGBT, 逆变器 (典型)

**switching losses IGBT, Inverter (typical)**

$E_{on} = f(R_G), E_{off} = f(R_G)$

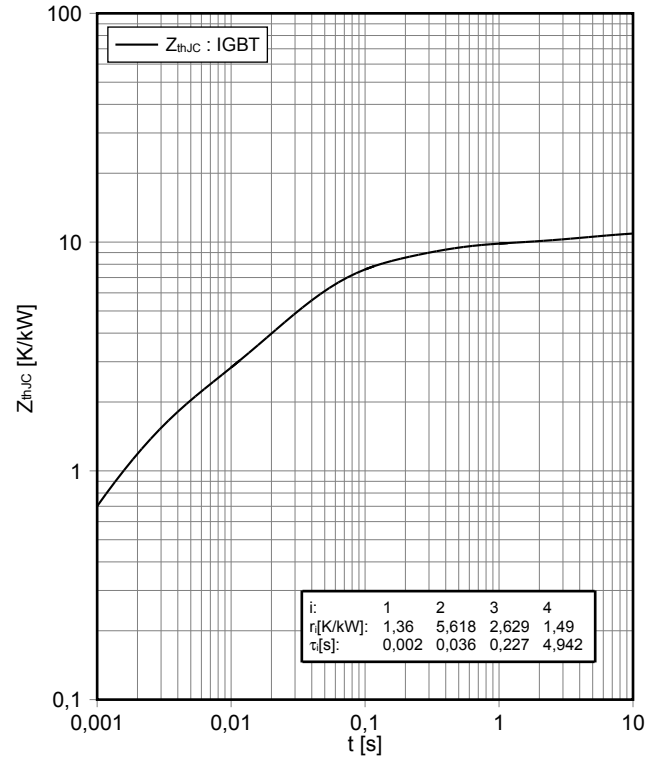
$V_{GE} = \pm 15 V, I_C = 1000 A, V_{CE} = 1800 V, C_{GE} = 220 nF$



瞬态热阻抗 IGBT, 逆变器

**transient thermal impedance IGBT, Inverter**

$Z_{thJC} = f(t)$

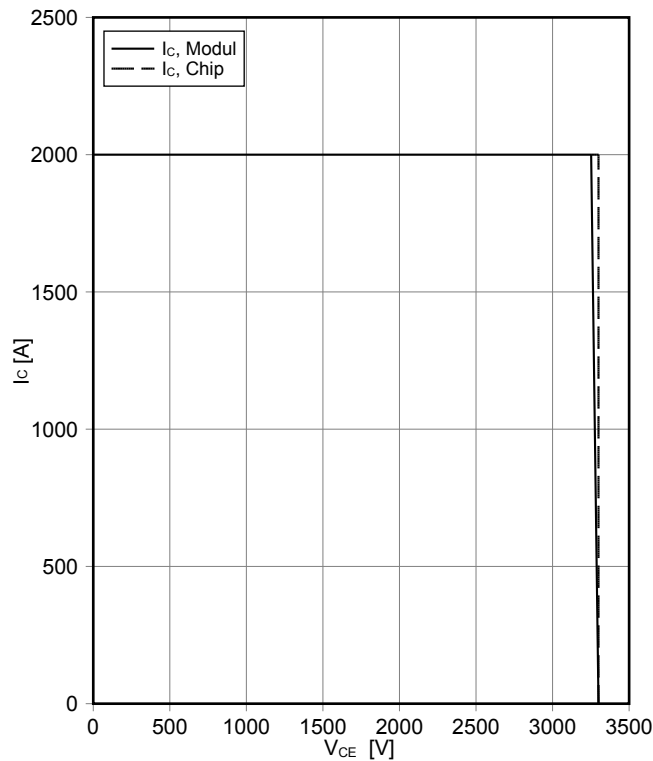


反偏安全工作区 IGBT, 逆变器 (RBSOA)

**reverse bias safe operating area IGBT, Inverter (RBSOA)**

$I_C = f(V_{CE})$

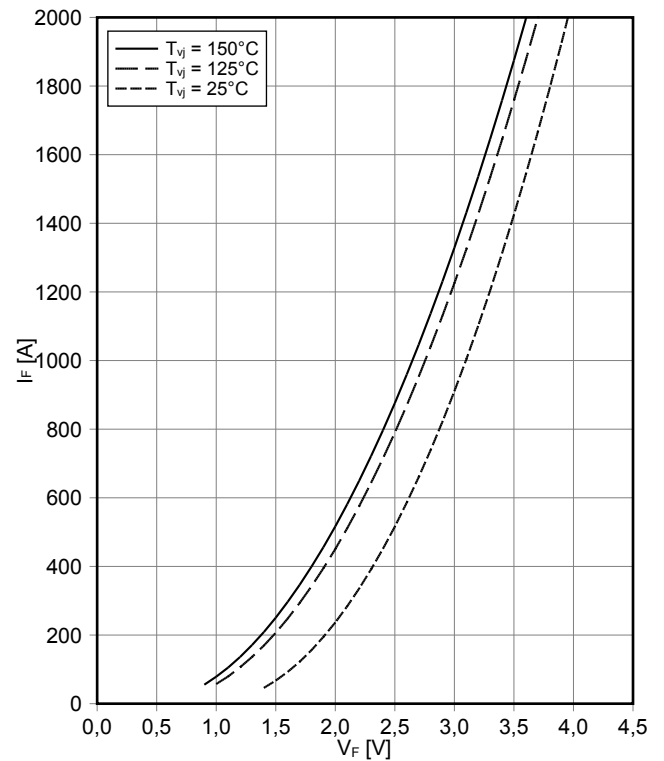
$V_{GE} = \pm 15 V, R_{Goff} = 2.3 \Omega, T_{vj} = 150^\circ C, C_{GE} = 220 nF$



正向偏压特性 二极管, 逆变器 (典型)

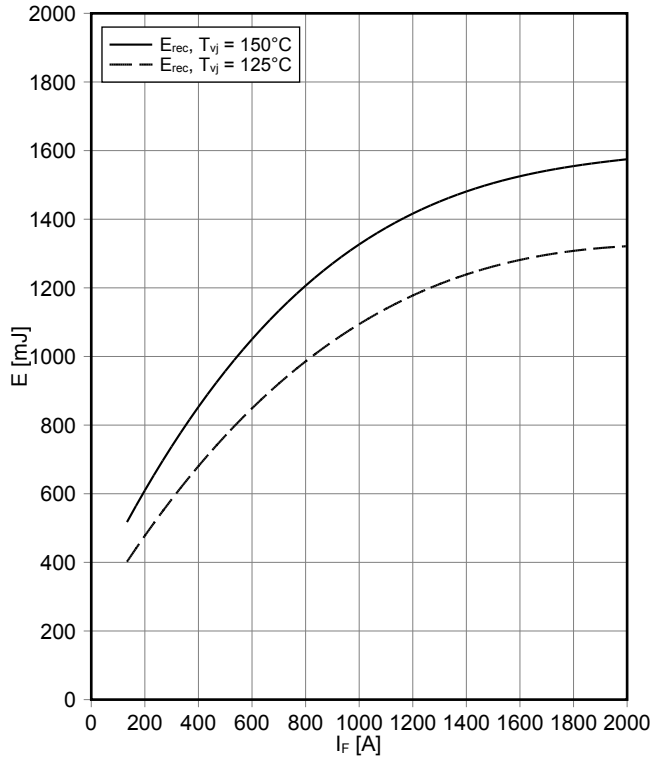
**forward characteristic of Diode, Inverter (typical)**

$I_F = f(V_F)$



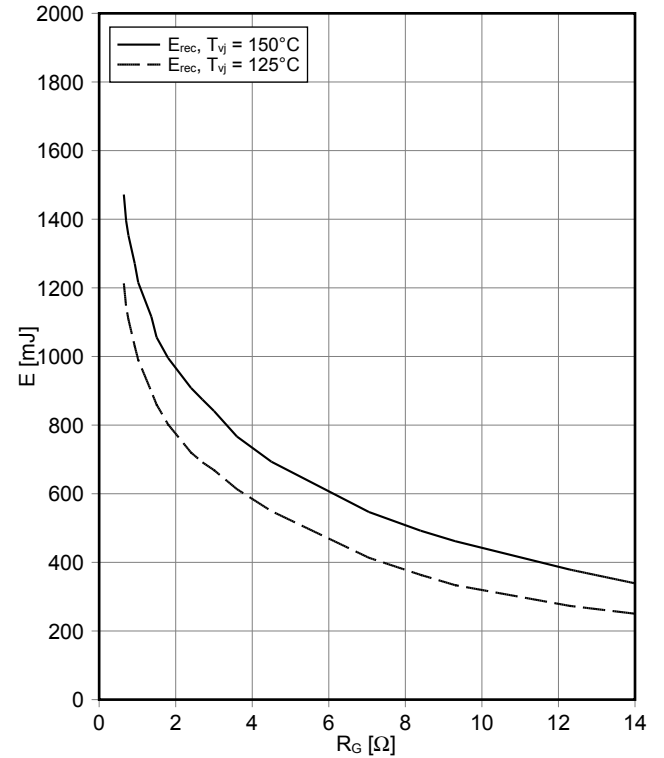
开关损耗 二极管,逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 0.71 \Omega, V_{CE} = 1800 V$



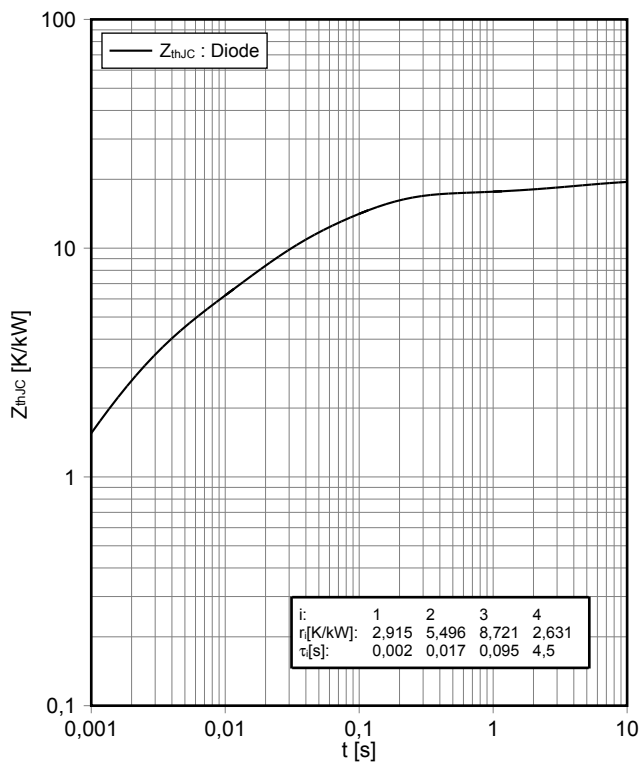
开关损耗 二极管,逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$   
 $I_F = 1000 A, V_{CE} = 1800 V$



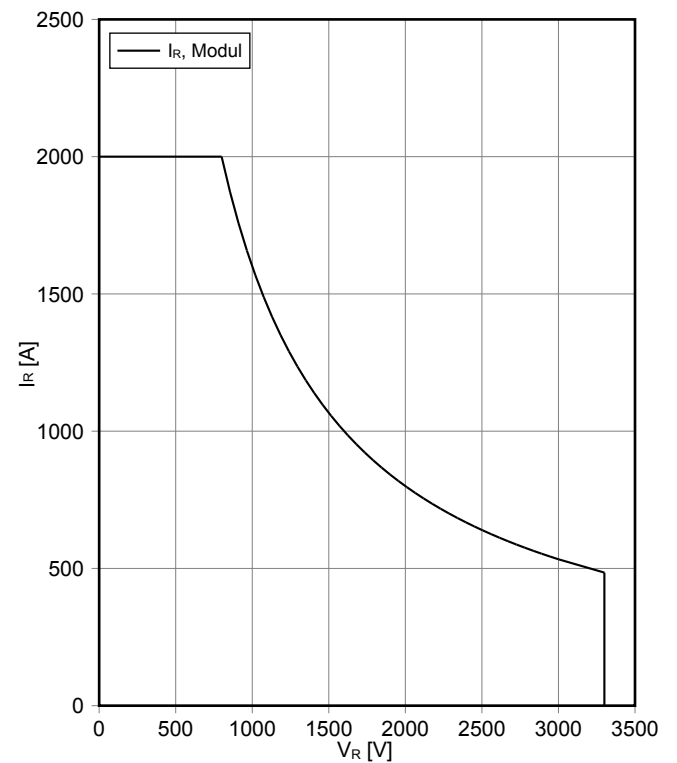
瞬态热阻抗 二极管,逆变器  
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

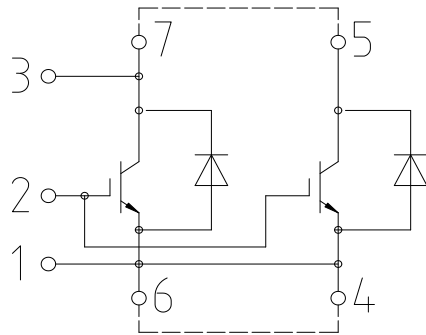


安全工作区 二极管,逆变器 (SOA)  
safe operation area Diode, Inverter (SOA)

$I_R = f(V_R)$   
 $T_{vj} = 150^\circ C$

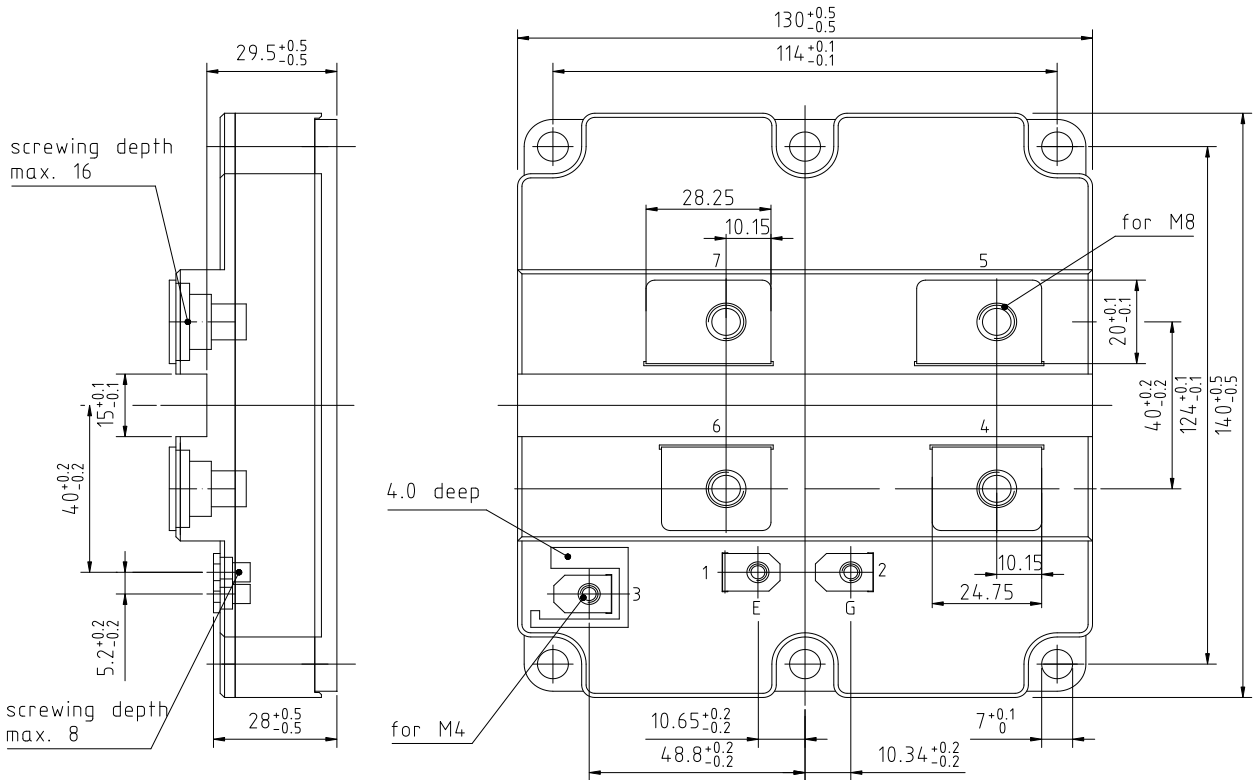
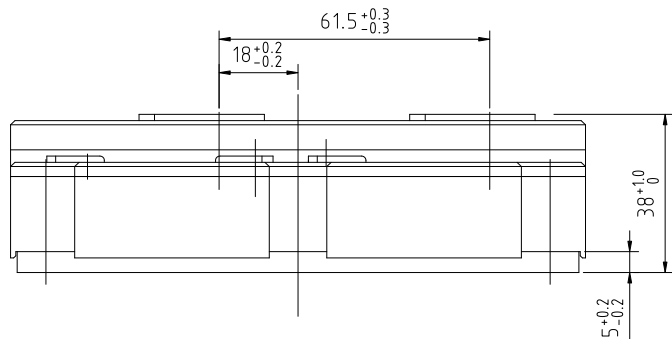


## 接线图 / Circuit diagram



external connection  
(to be done)

## 封装尺寸 / Package outlines





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